HETERO JUNCTION FIELD EFFECT TRANSISTOR **NE3514S02**

K BAND SUPER LOW NOISE AMPLIFIER N-CHANNEL HJ-FET

FEATURES

NEC

- Super low noise figure and high associated gain
 - NF = 0.75 dB TYP., G_a = 10 dB TYP. @ f = 20 GHz
- Micro-X plastic (S02) package

APPLICATIONS

- 20 GHz-band DBS LNB
- Other K-band communication systems

ORDERING INFORMATION

Part Number	Order Number	Package	Quantity	Marking	Supplying Form
NE3514S02-T1C	NE3514S02-T1C-A	S02 (Pb-Free)	2 kpcs/reel	D	• 8 mm wide embossed taping
NE3514S02-T1D	NE3514S02-T1D-A		10 kpcs/reel		• Pin 4 (Gate) faces the perforation side of the tape

Remark To order evaluation samples, contact your nearby sales office. Part number for sample order: NE3514S02

ABSOLUTE MAXIMUM RATINGS (TA = +25°C)

Parameter	Symbol	rmbol Ratings	
Drain to Source Voltage	VDS	4	V
Gate to Source Voltage	V _{GS}	-3	V
Drain Current	lo	loss	mA
Gate Current	lg	100	μA
Total Power Dissipation	Ptot Note	165	mW
Channel Temperature	Tch	+125	°C
Storage Temperature	Tstg	-65 to +125	°C

Note Mounted on 1.08 $\text{cm}^2 \times 1.0 \text{ mm}$ (t) glass epoxy PCB

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

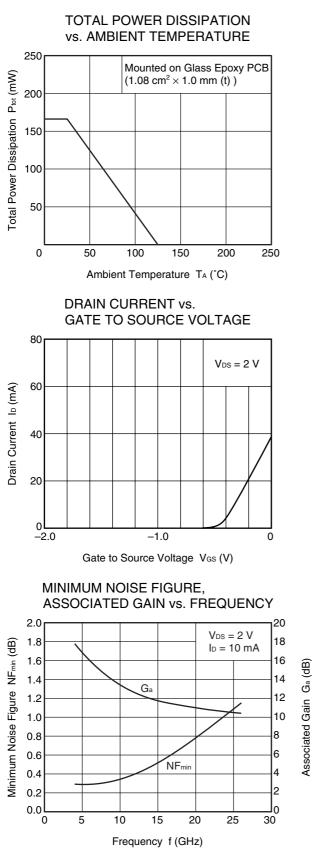
The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version. Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.

RECOMMENDED OPERATING CONDITIONS (TA = +25°C)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	VDS	1	2	3	V
Drain Current	lo	5	10	15	mA
Input Power	Pin	_	_	0	dBm

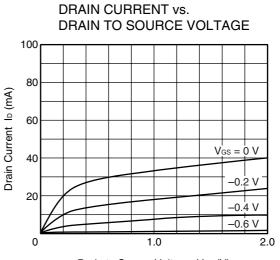
ELECTRICAL CHARACTERISTICS (T_A = +25°C, unless otherwise specified)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Gate to Source Leak Current	lgso	$V_{GS} = -3 V$	_	0.5	10	μA
Saturated Drain Current	loss	$V_{DS} = 2 V, V_{GS} = 0 V$	15	40	70	mA
Gate to Source Cutoff Voltage	VGS (off)	$V_{DS} = 2 V, I_{D} = 100 \mu A$	-0.2	-0.7	-2.0	V
Transconductance	Ят	V _{DS} = 2 V, I _D = 10 mA	40	55	-	mS
Noise Figure	NF	V _{DS} = 2 V, I _D = 10 mA, f = 20 GHz	_	0.75	1.0	dB
Associated Gain	Ga		8	10	-	dB



TYPICAL CHARACTERISTICS (TA = +25°C, unless otherwise specified)

Remark The graphs indicate nominal characteristics.



Drain to Source Voltage VDS (V)

S-PARAMETERS

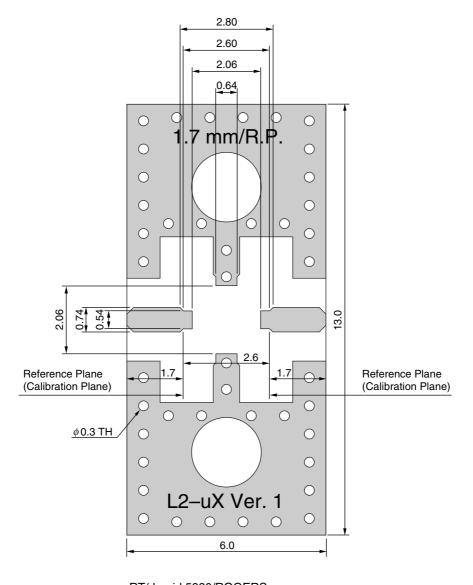
S-parameters/Noise parameters are provided on the NEC Compound Semiconductor Devices Web site in a form (S2P) that enables direct import to a microwave circuit simulator without keyboard input.

Click here to download S-parameters.

 $[\text{RF} \text{ and Microwave}] \rightarrow [\text{Device Parameters}]$

URL http://www.ncsd.necel.com/

RF MEASURING LAYOUT PATTERN (REFERENCE ONLY) (UNIT: mm)

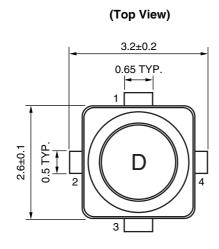


RT/duroid 5880/ROGERS t = 0.254 mm εr = 2.20

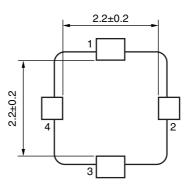
tan delta = 0.0009 @10 GHz

PACKAGE DIMENSIONS

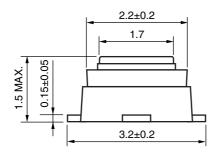
S02 (UNIT: mm)



(Bottom View)



(Side View)



PIN CONNECTIONS

- 1. Source
- 2. Drain
- 3. Source
- 4. Gate

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions		Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) Time at peak temperature Time at temperature of 220°C or higher Preheating time at 120 to 180°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 60 seconds or less : 120±30 seconds : 3 times : 0.2%(Wt.) or below	IR260
Partial Heating	Peak temperature (terminal temperature) Soldering time (per side of device) Maximum chlorine content of rosin flux (% mass)	: 350°C or below : 3 seconds or less : 0.2%(Wt.) or below	HS350

Caution Do not use different soldering methods together (except for partial heating).

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M8E 00.4-0110

Caution GaAs Products	This product uses gallium arsenide (GaAs). GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.
	• Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below.
	 Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials.
	2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal.
	• Do not burn, destroy, cut, crush, or chemically dissolve the product.
	• Do not lick the product or in any way allow it to enter the mouth.

► For further information, please contact

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